



US 1,603,200 (different near particles)  
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4 and laser

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Document ID	Class Date	Pages	Title	Current OR	Current Ref	Retrieval C	Inventor	S	C	F	3	2	4
US 20030071872	20030711	12	Wafer cleaning device, water	134/6	134/14;		Nishihara, Jun	P					US
A1			cleaning method and chemical		15/102;								US
US 20030027496	20030206	11	Method and apparatus for	451/36	451/533		Back, Gerald W. et al.	P					US
A1			probe tip cleaning and shape										US
US 20020170892	20021121	19	Dry surface cleaning	215/223.06	219/121.73;		Lee, Jong-Myung et al.	P					US
A1			apparatus using a laser		219/121.77								US
US 20020165637	20021107	32	Method for using an in situ	356/237.4	257/821.279;		Rossman, Kent et al.	P					US
A1			particle sensor for monitor		169/237.5;								US
US 20020194402	20020926	17	Article produced by acoustic	134/1	134/1.3		Madanshety, Saneer F.	P					US
A1			cavitation in a liquid medium										US
US 20020106631	20020815	16	Single-transducer ACM	134/1	134/184		Madanshety, Saneer I.	P					US
A1			method and apparatus										US
US 20020089946	20020314	24	Method and apparatus for	204/157.15	422/136		Allen, Susan Davin	P					US
A1			removing minute particles fr										US
US 6635045	02	20031021	9	Dry surface cleaning	219/121.66	219/121.73;	Lee, Jong-Myung et al.	P					US
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US 6546941	R1	20030415	12	Wafer cleaning device, water	134/157	134/992							US
			cleaning method and chemical				Nishihara, Jun	P					US
US 6355056	01	20020526	17	Single transducer ACM	134/1	134/194;	Madanshety, Saneer I.	P					US
			method and apparatus		134/992;								US
US 6078534	B1	20020430	26	Semiconductor wafer cleaning	134/1.3	134/18;	Olesen, Michael B. et al.	P					US
						134/2;							US
US 6150445	A	20001212	24	Semiconductor wafer cleaning	134/1.3	134/2;	Olesen, Michael B. et al.	P					US
			method		134/2;								US
US 6025206	A	20000615	3	Method for detecting defects	438/16	250/559.41;	Chen, Jai-Hua et al.	P					US
						257/821.525;							US
US 5996595	A	19991207	22	Semiconductor wafer cleaning	134/1.3	134/2;	Olesen, Michael B. et al.	P					US
			system		216/99;								US
US 5950645	A	19980914	25	Semiconductor wafer cleaning	134/98.1	134/100.3;	Olesen, Michael B. et al.	P					US
			system			134/113;							US
US 5908509	A	19990601	23	Semiconductor wafer cleaning	134/1.3	134/2;	Olesen, Michael B. et al.	P					US
			system			134/26;							US
US 5656097	A	19980912	25	Semiconductor wafer cleaning	134/1	134/2;	Olesen, Michael B. et al.	P					US
			system			134/26;							US
US 4986533	A	19910129	83	Method for deposition of	427/563	427/294;	Freeman, Dean W. et al.	P					US
			silicon oxide on a wafer		427/532;								US
US 4910643	A	19901130	31	Precleaning apparatus and	427/563	118/722;	Freeman, Dean W. et al.	P					US
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